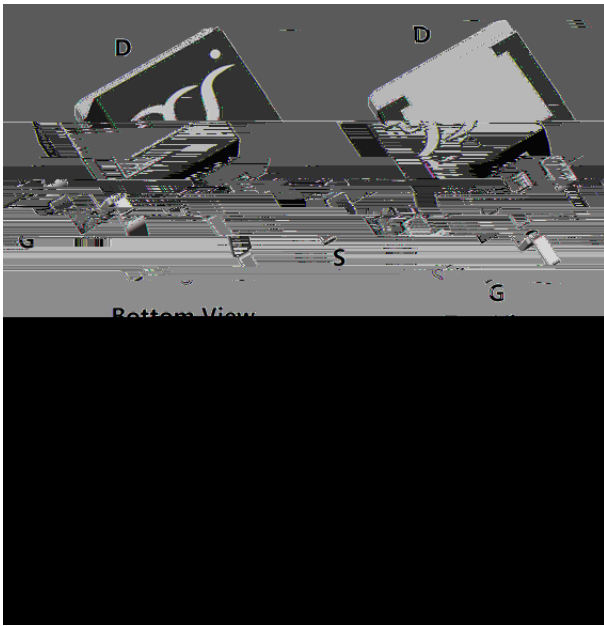




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

• V_{DS}	40V	T
• I_D	126A	
• $R_{DS(ON)}$		

	$T_A=25$	I_D	26	A
	$T_A=100$		18	
	$T_C=25$		126	
	$T_C=100$		89	
Pulsed Drain Current ^A		I_{DM}	400	A
Avalanche energy ^B		EAS	156	mJ
Total Power Dissipation ^C	$T_A=25$	P_D	3.7	W
	$T_A=100$		1.8	
	$T_C=25$		83	
	$T_C=100$		41	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +175	

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	33	40	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.5	1.8	

■ Ordering Information (Example)

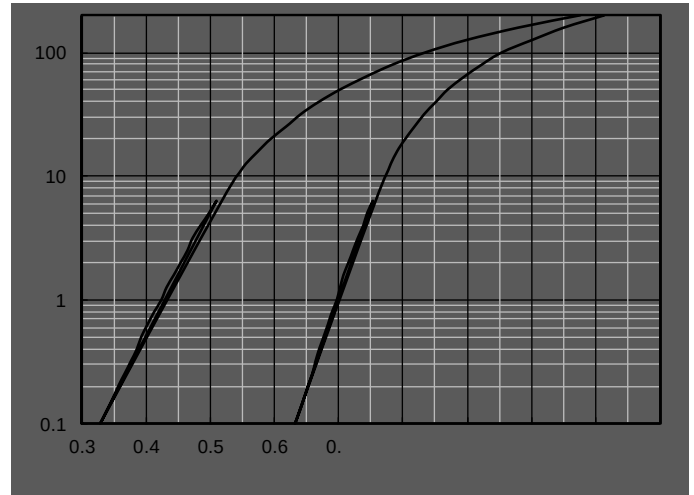
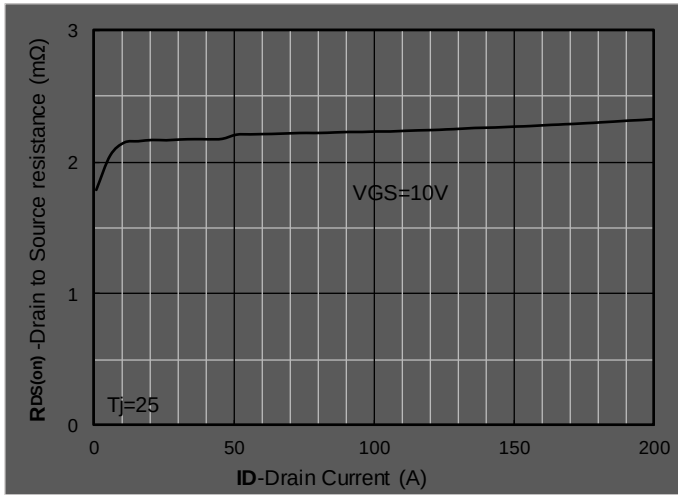
PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB3D0G04HQ	F2	YJB3D0G04H	800	/	8000	13" reel

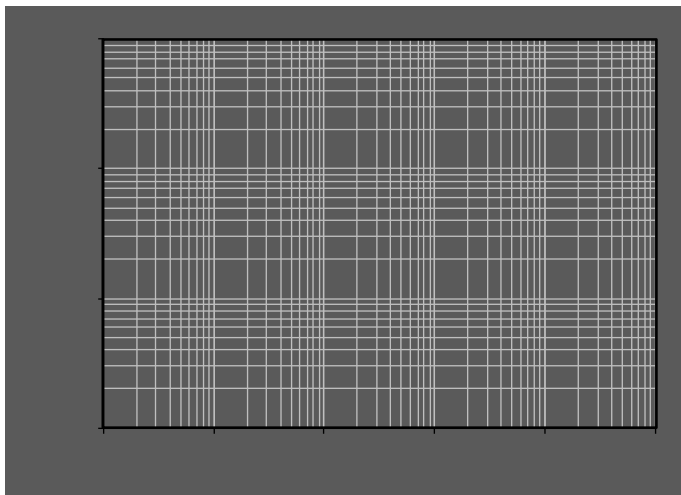


■Typical Electrical and Thermal Characteristics Diagrams



YJB3D0G04HQ







■ TO-263-HY Package information

DIMENSIONS					
SYMBOL	INCHES				
	MIN.	NOM.			
A1	0.000				
A2	0.174	0.180			
b	0.028	0.032			
b2	0.046	0.050			
c	0.013	0.015			
c2					
D1					
D2	0.303	0.315			
E	0.571	0.591			
E1	0.337	0.3			

